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Kind regards,

Team Nexperia

BC807; BC807W; BC327 45 V, 500 mA PNP general-purpose transistors Rev. 06 — 17 November 2009

Product data sheet

Product profile 1.

1.1 General description

PNP general-purpose transistors.

Table 1. **Product overview**

Type number	Package	Package				
	NXP	JEITA	_			
BC807	SOT23	-	BC817			
BC807W	SOT323	SC-70	BC817W			
BC327[1]	SOT54 (TO-92)	SC-43A	BC337			

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- High current
- Low voltage

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base; I _C = 10 mA		-	-	-45	V
I _C	collector current (DC)			-	-	-500	mΑ
I _{CM}	peak collector current			-	-	-1	Α
h _{FE}	DC current gain	$I_C = -100 \text{ mA};$ $V_{CE} = -1 \text{ V}$	[1]				
	BC807; BC807W; BC327			100	-	600	
	BC807-16; BC807-16W; BC327-16			100	-	250	
	BC807-25; BC807-25W; BC327-25			160	-	400	
	BC807-40; BC807-40W; BC327-40			250	-	600	

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



2. Pinning information

Pin	Description	Simplified outline	Symbol
SOT23			-
1	base		
2	emitter	3	;
3	collector		1—
		1	Γκ.
			sym01:
SOT323			Symon
1	base		
2	emitter	3	;
3	collector		. V
•	odilottoi		1—
			2
		1 2	sym01
		sot323_so	
SOT54			
1	emitter		
2	base		
3	collector		2 —
		001aab347	006aaa14
SOT54A			
1	emitter		
2	base		
3	collector	A	2 —
			''
		3 001aab348	006aaa14
SOT54 v	ariant		0000007
1	emitter		
2	base	TE:	
3	collector		2 —
			- T
		001aab447	
			006aaa1

3. Ordering information

Table 4. Ordering information

Type number[1]	Package	ackage							
	Name	Description	Version						
BC807	-	plastic surface mounted package; 3 leads	SOT23						
BC807W	SC-70	plastic surface mounted package; 3 leads	SOT323						
BC327 ^[2]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54						

^[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BC807	5D*
BC807-16	5A*
BC807-25	5B*
BC807-40	5C*
BC807W	5D*
BC807-16W	5A*
BC807-25W	5B*
BC807-40W	5C*
BC327	C327
BC327-16	C32716
BC327-25	C32725
BC327-40	C32740

^{[1] * = -:} made in Hong Kong

^[2] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base; I _C = 10 mA	-	–45	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current (DC)		-	-500	mA
I _{CM}	peak collector current		-	-1	Α
I _{BM}	peak base current		-	-200	mA
P _{tot}	total power dissipation				
	BC807	$T_{amb} \le 25 ^{\circ}C$	[1][2]	250	mW
	BC807W	$T_{amb} \le 25 ^{\circ}C$	[1][2] _	200	mW
	BC327	$T_{amb} \le 25 ^{\circ}C$	[1][2] _	625	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

^[1] Transistor mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ιι () α)	thermal resistance from junction to ambient					
	BC807	$T_{amb} \le 25 ^{\circ}C$	[1][2]	-	500	K/W
	BC807W	$T_{amb} \le 25 ^{\circ}C$	[1][2] _	-	625	K/W
	BC327	$T_{amb} \le 25 ^{\circ}C$	[1][2]	-	200	K/W

^[1] Transistor mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

^[2] Valid for all available selection groups.

^[2] Valid for all available selection groups.

7. Characteristics

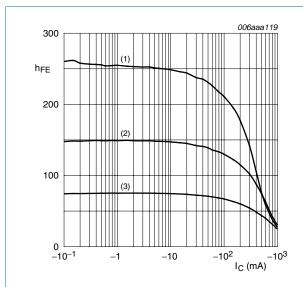
Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Parameter	Conditions	Min	Тур	Max	Unit
collector-base cut-off current	$I_E = 0 \text{ A}; V_{CB} = -20 \text{ V}$	-	-	-100	nA
	$I_E = 0 \text{ A}; V_{CB} = -20 \text{ V};$ $T_j = 150 \text{ °C}$	-	-	– 5	μА
emitter-base cut-off current	$I_C = 0 A; V_{EB} = -5 V$	-	-	-100	nΑ
DC current gain	$I_C = -100 \text{ mA}; V_{CE} = -1 \text{ V}$	[1]			
BC807; BC807W; BC327		100	-	600	
BC807-16; BC807-16W; BC327-16		100	-	250	
BC807-25; BC807-25W; BC327-25		160	-	400	
BC807-40; BC807-40W; BC327-40		250	-	600	
DC current gain	$I_C = -500 \text{ mA}; V_{CE} = -1 \text{ V}$	<u>[1]</u> 40	-	-	
collector-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	[1] -	-	-700	mV
base-emitter voltage	$I_C = -500 \text{ mA}; V_{CE} = -1 \text{ V}$	[2]	-	-1.2	V
collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz	-	5	-	pF
transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	80	-	-	MHz
	emitter-base cut-off current DC current gain BC807; BC807W; BC327 BC807-16; BC807-16W; BC327-16 BC807-25; BC807-25W; BC327-25 BC807-40; BC807-40W; BC327-40 DC current gain collector-emitter saturation voltage base-emitter voltage collector capacitance	$\begin{tabular}{l} \begin{tabular}{l} tabu$	$ \begin{array}{c} \text{collector-base cut-off current} & I_{E} = 0 \text{ A; } V_{CB} = -20 \text{ V} \\ \hline I_{E} = 0 \text{ A; } V_{CB} = -20 \text{ V; } \\ \hline I_{T} = 150 \text{ °C} \\ \hline \\ \text{emitter-base cut-off current} & I_{C} = 0 \text{ A; } V_{EB} = -5 \text{ V} \\ \hline \\ \text{DC current gain} & I_{C} = -100 \text{ mA; } V_{CE} = -1 \text{ V} \\ \hline \\ \text{BC807; BC807W; BC327} & 100 \\ \hline \\ \text{BC807-16; BC807-16W; } \\ \text{BC327-16} & 100 \\ \hline \\ \text{BC327-16} & 160 \\ \hline \\ \text{BC807-25; BC807-25W; } \\ \text{BC327-25} & 160 \\ \hline \\ \text{DC current gain} & I_{C} = -500 \text{ mA; } V_{CE} = -1 \text{ V} \\ \text{Collector-emitter saturation} \\ \text{Voltage} & I_{C} = -500 \text{ mA; } V_{CE} = -1 \text{ V} \\ \text{Collector capacitance} & I_{C} = -500 \text{ mA; } V_{CE} = -1 \text{ V} \\ \text{Collector capacitance} & I_{C} = -500 \text{ mA; } V_{CE} = -1 \text{ V} \\ \text{Collector capacitance} & I_{C} = -500 \text{ mA; } V_{CE} = -1 \text{ V} \\ \text{Collector capacitance} & I_{C} = -500 \text{ mA; } V_{CE} = -1 \text{ V} \\ \text{Collector capacitance} & I_{C} = -500 \text{ mA; } V_{CE} = -1 \text{ V} \\ \text{Collector capacitance} & I_{C} = -500 \text{ mA; } V_{CE} = -1 \text{ V} \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -10 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{S0} & \text{S0} \\ \hline \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ \text{Collector capacitance} & I_{C} = -10 \text{ mA; } V_{CE} = -5 \text{ V; } \\ Collector capacitan$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

^[2] V_{BE} decreases by approximately 2 mV/K with increasing temperature.



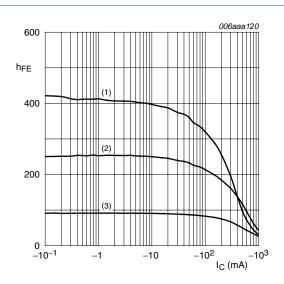
$$V_{CE} = -1 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 1. Selection -16: DC current gain as a function of collector current; typical values



$$V_{CE} = -1 V$$

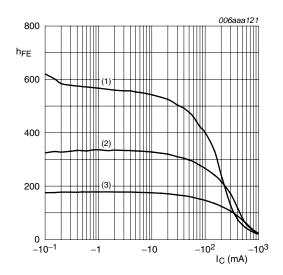
(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 2. Selection -25: DC current gain as a function of collector current; typical values

6 of 19



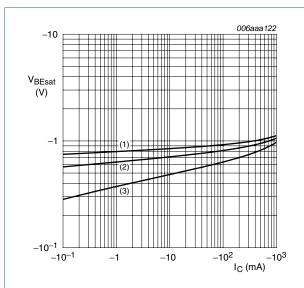
$$V_{CE} = -1 V$$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Selection -40: DC current gain as a function of collector current; typical values Fig 3.



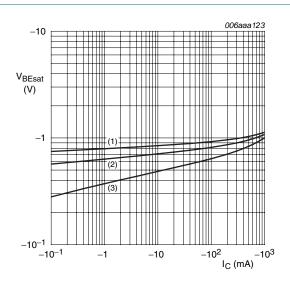
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. Selection -16: Base-emitter saturation voltage as a function of collector current; typical values



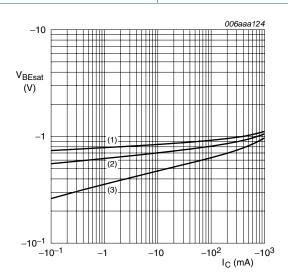
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 5. Selection -25: Base-emitter saturation voltage as a function of collector current; typical values



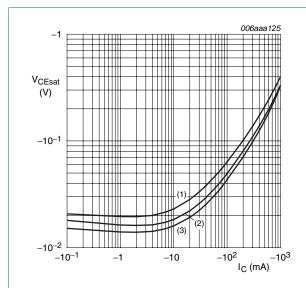
 $I_{\rm C}/I_{\rm B}=10$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 6. Selection -40: Base-emitter saturation voltage as a function of collector current; typical values



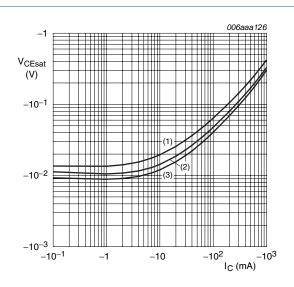
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Selection -16: Collector-emitter saturation voltage as a function of collector current; typical values



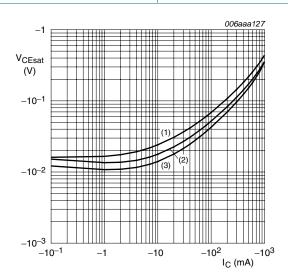
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

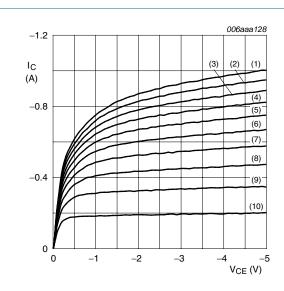
Fig 8. Selection- 25: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B}=10$$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) T_{amb} = 25 °C
- (3) $T_{amb} = -55 \, ^{\circ}C$

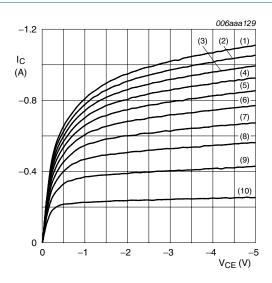
Fig 9. Selection -40: Collector-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

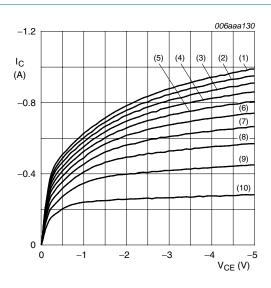
- (1) $I_B = -16.0 \text{ mA}$
- (2) $I_B = -14.4 \text{ mA}$
- (3) $I_B = -12.8 \text{ mA}$
- (4) $I_B = -11.2 \text{ mA}$
- (5) $I_B = -9.6 \text{ mA}$
- (6) $I_B = -8.0 \text{ mA}$
- (7) $I_B = -6.4 \text{ mA}$
- (8) $I_B = -4.8 \text{ mA}$
- (9) $I_B = -3.2 \text{ mA}$
- (10) $I_B = -1.6 \text{ mA}$

Fig 10. Selection -16: Collector current as a function of collector-emitter voltage; typical values



T_{amb} = 25 °C

- (1) $I_B = -13.0 \text{ mA}$
- (2) $I_B = -11.7 \text{ mA}$
- (3) $I_B = -10.4 \text{ mA}$
- (4) $I_B = -9.1 \text{ mA}$
- (5) $I_B = -7.8 \text{ mA}$
- (6) $I_B = -6.5 \text{ mA}$
- (7) $I_B = -5.2 \text{ mA}$
- (8) $I_B = -3.9 \text{ mA}$
- (9) $I_B = -2.6 \text{ mA}$ (10) $I_B = -1.3 \text{ mA}$
- Fig 11. Selection -25: Collector current as a function of collector-emitter voltage; typical values



T_{amb} = 25 °C

- (1) $I_B = -12.0 \text{ mA}$
- (2) $I_B = -10.8 \text{ mA}$
- (3) $I_B = -9.6 \text{ mA}$
- (4) $I_B = -8.4 \text{ mA}$
- (5) $I_B = -7.2 \text{ mA}$
- (6) $I_B = -6.0 \text{ mA}$
- (7) $I_B = -4.8 \text{ mA}$ (8) $I_B = -3.6 \text{ mA}$
- (9) $I_B = -2.4 \text{ mA}$
- (5) IB = 2.4 III/
- (10) $I_B = -1.2 \text{ mA}$

Fig 12. Selection -40: Collector current as a function of collector-emitter voltage; typical values

8. Package outline

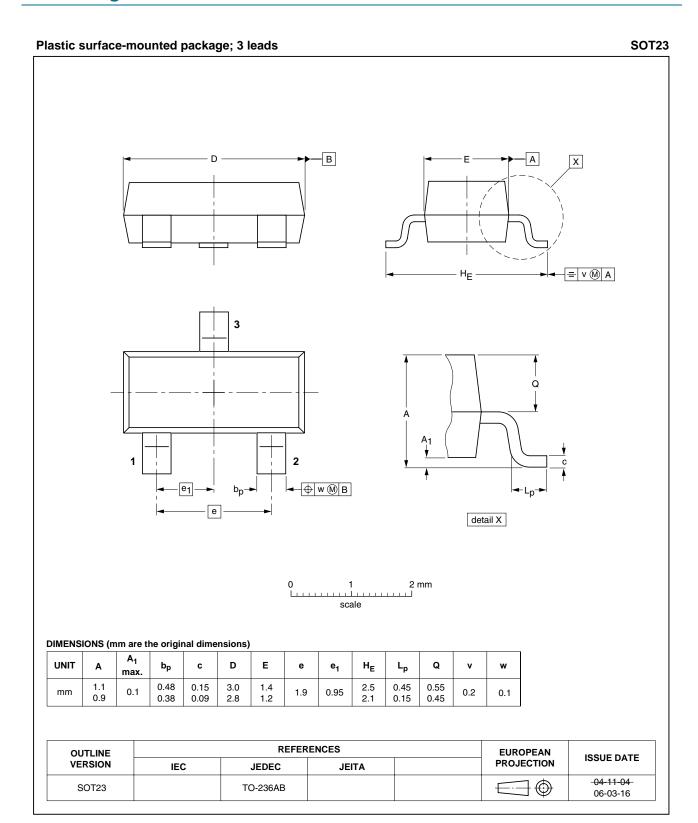


Fig 13. Package outline SOT23 (TO-236AB)

BC807_BC807W_BC327_6 © NXP B.V. 2009. All rights reserved.

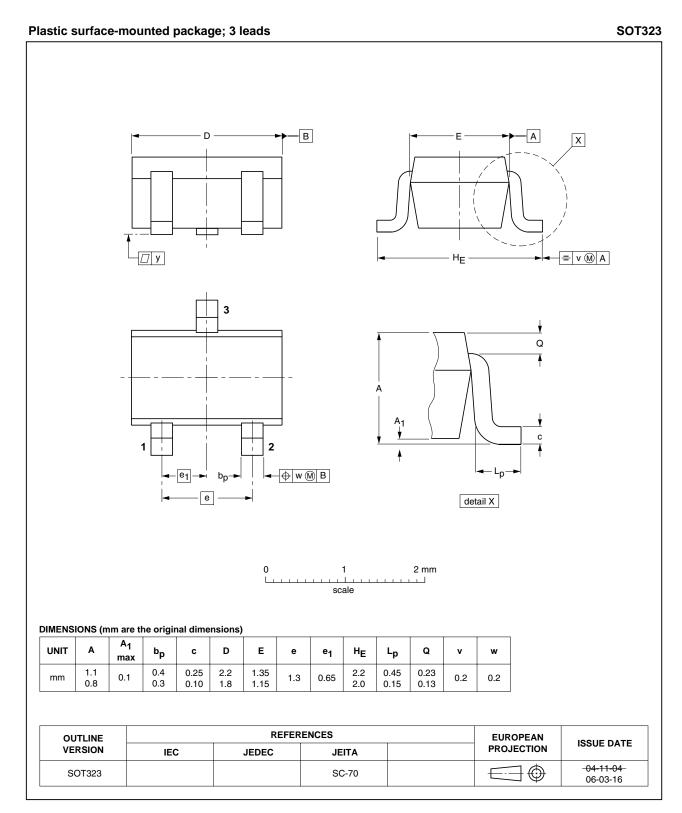
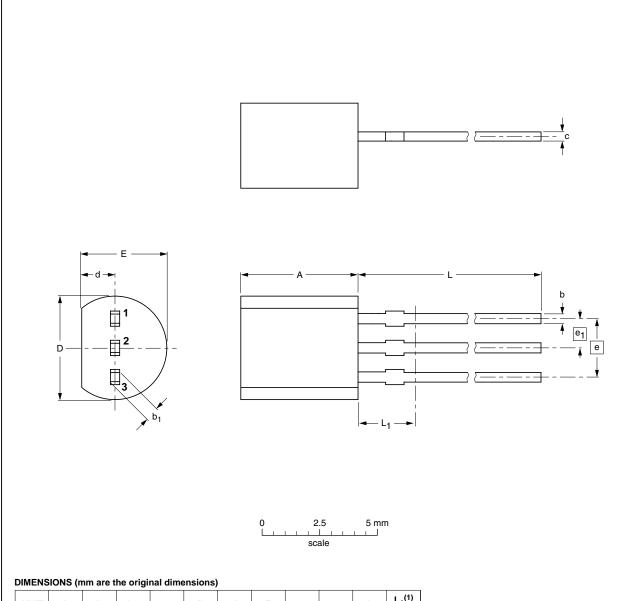


Fig 14. Package outline SOT323 (SC-70)

BC807_BC807W_BC327_6

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

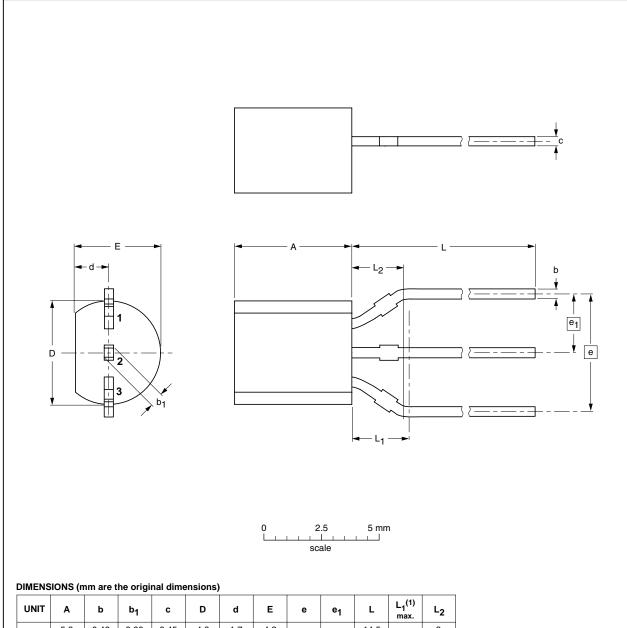
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A		-04-06-28- 04-11-16

Fig 15. Package outline SOT54 (SC-43A/TO-92)

BC807_BC807W_BC327_6

Plastic single-ended leaded (through hole) package; 3 leads (wide pitch)

SOT54A



UNIT	Α	b	b ₁	С	D	d	Е	е	e ₁	L	L ₁ ⁽¹⁾ max.	L ₂
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	5.08	2.54	14.5 12.7	3	3 2

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

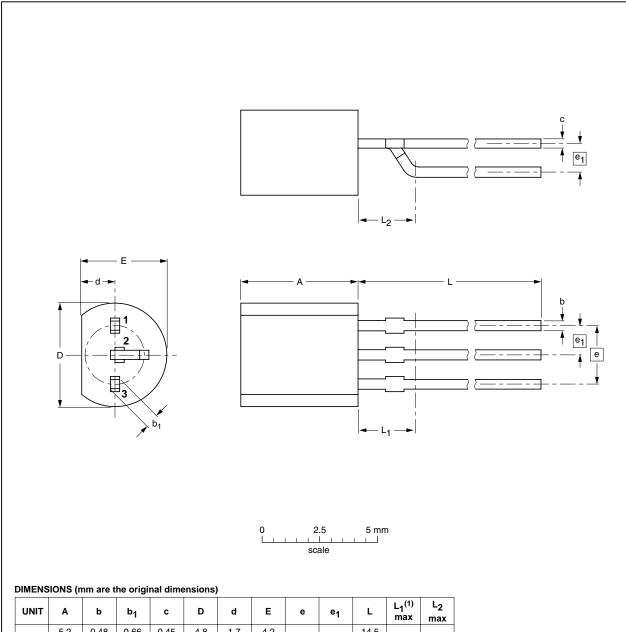
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT54A					97-05-13 04-06-28	

Fig 16. Package outline SOT54A

BC807_BC807W_BC327_6 © NXP B.V. 2009. All rights reserved.

Plastic single-ended leaded (through hole) package; 3 leads (on-circle)

SOT54 variant



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max	L ₂ max	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	2.5	

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54 variant						04-06-28 05-01-10

Fig 17. Package outline SOT54 variant

BC807_BC807W_BC327_6 © NXP B.V. 2009. All rights reserved.

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity		
			3000	5000	10000	
BC807	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
BC807W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	
BC327	SOT54	bulk, straight leads	-	-412	-	
BC327	SOT54A	tape and reel, wide pitch	-	-	-116	
BC327	SOT54A	tape ammopack, wide pitch	-	-	-126	
BC327	SOT 54 variant	bulk, delta pinning (on-circle)	-	-112	-	

^[1] For further information and the availability of packing methods, see Section 12.

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
BC807_BC807W_ BC327_6	20091117	Product data sheet	-	BC807_BC807W_ BC327_5				
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconducto including new legal definitions and disclaimers. No changes were made to the techn content. <u>Table 3 "Pinning"</u>: updated Figure 13 "Package outline SOT23 (TO-236AB)": updated 							
	• Figure 14 "Package outline SOT323 (SC-70)": updated							
BC807_BC807W_ BC327_5	20050221	Product data sheet	CPCN200302007F CPCN200405006F	BC807_4; BC807W_3; BC327_3				
BC807_4	20040116	Product specification	-	BC807_3				
BC807W_3	19990518	Product specification	-	BC807W_808W_CNV_2				
BC327_3	19990415	Product specification	-	BC327_2				

BC807; BC807W; BC327

45 V, 500 mA PNP general-purpose transistors

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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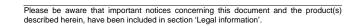
12. Contact information

For more information, please visit: http://www.nxp.com

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